

SBOS155A - AUGUST 1987 - REVISED OCTOBER 2002

High-Speed Precision Difet® OPERATIONAL AMPLIFIER

FEATURES

WIDE BANDWIDTH: 6.5MHz
 HIGH SLEW RATE: 35V/µs
 LOW OFFSET: ±250µV max

LOW BIAS CURRENT: ±1pA max
 FAST SETTLING TIME: 1µs to 0.01%

• UNITY-GAIN STABLE

DESCRIPTION

The OPA602 is a precision, wide bandwidth FET operational amplifier. Monolithic *Difet* (dielectrically isolated FET) construction provides an unusual combination of high-speed and accuracy.

Its wide-bandwidth design minimizes dynamic errors. High slew rate and fast settling time allow accurate signal processing in pulse and data conversion applications. Wide bandwidth and low distortion minimize AC errors. All specifications are rated with a 1k Ω resistor in parallel with 500pF load. The OPA602 is unity-gain stable and easily drives capacitive loads up to 1500pF.

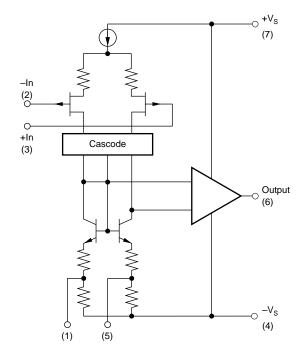
Laser-trimmed input circuitry provides offset voltage and drift performance normally associated with precision bipolar op amps. **Difet** construction achieves extremely low input bias currents (1pA max) without compromising input voltage noise.

The OPA602's unique input cascode circuitry maintains low input bias current and precise input characteristics over its full input common-mode voltage range.

Difet® Burr-Brown Corp.

APPLICATIONS

- PRECISION INSTRUMENTATION
- OPTOELECTRONICS
- SONAR, ULTRASOUND
- PROFESSIONAL AUDIO EQUIPMENT
- MEDICAL EQUIPMENT
- DATA CONVERSION





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



ABSOLUTE MAXIMUM RATINGS(1)

Supply Voltage	±18V _{DC}
Internal Power Dissipation (T _J ≤ +175°C)	1000mW
Differential Input Voltage	Total V _S
Input Voltage Range	±V _S
Storage Temperature Range	_
P and U Packages4	10°C to +125°C
Operating Temperature Range	
P and U Packages	25°C to + 85°C
Lead Temperature	
U Package, SO (3s)	+260°C
Output Short-Circuit to Ground (+25°C)	Continuous
Junction Temperature	+175°C

NOTE: (1) Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods may affect device reliability.

ELECTROSTATIC DISCHARGE SENSITIVITY

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

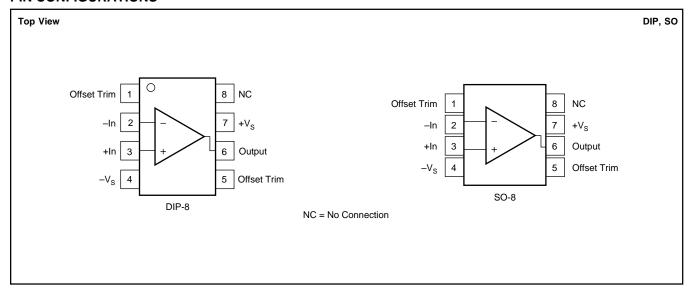
ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

PACKAGE/ORDERING INFORMATION

PRODUCT	OFFSET VOLTAGE MAX (μV) AT 25°C	PACKAGE-LEAD	PACKAGE DESIGNATOR ⁽¹⁾	SPECIFIED TEMPERATURE RANGE	PACKAGE MARKING	ORDERING NUMBER	TRANSPORT MEDIA, QUANTITY
OPA602AP	±2000	DIP-8	Р	−25°C to +85°C	602AP	602AP	Tubes, 50
OPA602BP	±1000	"	"	II .	602BP	602BP	Tubes, 50
OPA602AU	±3000	SO-8	D	–25°C to +85°C	602AU	602AU	Tubes, 100

NOTE: (1) For the most current specifications and package information, refer to our web site at www.ti.com.

PIN CONFIGURATIONS



ELECTRICAL CHARACTERISTICS

At $V_S = \pm 15 V_{DC}$ and $T_A = +25^{\circ}C$, unless otherwise noted.

PARAMETER NPUT NOISE Voltage: $f_O = 10Hz$ $f_O = 100Hz$ $f_O = 10Hz$ $f_O = 10Hz$ $f_B = 10Hz$ to $10Hz$ $f_B = 0.1Hz$ to $10Hz$ Current: $f_B = 0.1Hz$ to $10Hz$ $f_O = 0.1Hz$ to $20Hz$ DFFSET VOLTAGE nput Offset Voltage: P Package	CONDITIONS	MIN	23 19 13 12 1.4 0.95	MAX	MIN	* *	MAX	UNITS nV/√Hz
Voltage: $f_O = 10\text{Hz}$ $f_O = 10\text{Hz}$ $f_O = 10\text{Hz}$ $f_O = 16\text{Hz}$ $f_O = 16\text{Hz}$ $f_B = 10\text{Hz} \text{ to } 10\text{Hz}$ $f_B = 0.1\text{Hz} \text{ to } 10\text{Hz}$ $f_B = 0.1\text{Hz} \text{ to } 10\text{Hz}$ $f_D = 0.1\text{Hz} \text{ to } 20\text{Hz}$ Current: $f_D = 0.1\text{Hz} \text{ to } 20\text{Hz}$ DFFSET VOLTAGE nput Offset Voltage:			19 13 12 1.4					n\//\ \\ -
f_O = 10Hz f_O = 10Hz f_O = 10kHz f_O = 10kHz f_B = 10Hz to 10kHz f_B = 0.1Hz to 10Hz Current: f_B = 0.1Hz to 10Hz f_O = 0.1Hz to 20kHz DFFSET VOLTAGE nput Offset Voltage:			19 13 12 1.4					n\//5\□-
$f_O = 100$ Hz $f_O = 1$ kHz $f_O = 10$ kHz $f_B = 10$ Hz to 10 kHz $f_B = 0.1$ Hz to 10 Hz Current: $f_B = 0.1$ Hz to 10 Hz $f_O = 0.1$ Hz to 20 kHz DFFSET VOLTAGE nput Offset Voltage:			19 13 12 1.4					DV//\\\
$f_O = 1 \text{kHz}$ $f_O = 10 \text{kHz}$ $f_B = 10 \text{Hz}$ to 10kHz $f_B = 0.1 \text{Hz}$ to 10Hz Current: $f_B = 0.1 \text{Hz}$ to 10Hz $f_O = 0.1 \text{Hz}$ to 20kHz DFFSET VOLTAGE nput Offset Voltage:			13 12 1.4			*		
$f_O = 1 \text{kHz}$ $f_O = 10 \text{kHz}$ $f_B = 10 \text{Hz}$ to 10kHz $f_B = 0.1 \text{Hz}$ to 10Hz Current: $f_B = 0.1 \text{Hz}$ to 10Hz $f_O = 0.1 \text{Hz}$ to 20kHz DFFSET VOLTAGE nput Offset Voltage:			12 1.4		1	-^		nV/√Hz
$f_O^-=10 \text{kHz}$ $f_B=10 \text{Hz}$ to 10kHz $f_B=0.1 \text{Hz}$ to 10Hz Current: $f_B=0.1 \text{Hz}$ to 10Hz $f_O=0.1 \text{Hz}$ to 20kHz DFFSET VOLTAGE nput Offset Voltage:			12 1.4			*		nV/√Hz
$f_B = 10$ Hz to 10kHz $f_B = 0.1$ Hz to 10Hz Current: $f_B = 0.1$ Hz to 10Hz $f_O = 0.1$ Hz to 20kHz DFFSET VOLTAGE nput Offset Voltage:			1.4	i		*		nV/√Hz
$f_B = 0.1$ Hz to 10Hz Current: $f_B = 0.1$ Hz to 10Hz $f_O = 0.1$ Hz to 20kHz DFFSET VOLTAGE nput Offset Voltage:						*		μVrms
Current: f _B = 0.1Hz to 10Hz f _O = 0.1Hz to 20kHz DFFSET VOLTAGE nput Offset Voltage:			11145			*		μVp-p
f_B = 0.1Hz to 10Hz f_O = 0.1Hz to 20kHz DFFSET VOLTAGE nput Offset Voltage:			0.33					μνρ-ρ
f _O = 0.1Hz to 20kHz DFFSET VOLTAGE nput Offset Voltage:			40			.,		£0
OFFSET VOLTAGE nput Offset Voltage:		I	12			*		fAp-p fA/√Hz
nput Offset Voltage:			0.6			*		TA/ √⊓Z
P Package								1
			0.5	1		1	2	mV
U Package						1	3	mV
Over Specified Temperature						1		
P, U Packages		1	±0.75	±1.5		±1.5		mV
Average Drift ⁽¹⁾	T T., +0.T	1	±3	±1.5 ±5		±1.5 *	±15	μV/°C
9	$T_A = T_{MIN}$ to T_{MAX}			±ο	70		±15	
Supply Rejection	$\pm V_S = 12V \text{ to } 18V$	80	100		70	*		dB
BIAS CURRENT								ĺ
nput Bias Current	$V_{CM} = 0V_{DC}$		±1	±2		±2	±10	pА
Over Specified Temperature			±20	±200		±20	±500	pА
OFFSET CURRENT								
nput Offset Current	$V_{CM} = 0V_{DC}$		0.5	2		1	10	pА
Over Specified Temperature	I CM SIDC		20	200		20	500	pΑ
<u> </u>				200			- 000	Pri
NPUT IMPEDANCE								l
Differential			10 ¹³ 1			*		Ω pF
Common-Mode			1014 3			*		Ω pF
NPUT VOLTAGE RANGE								
Common-Mode Input Range		±10.2	+13, -11		*	*		V
Common-Mode Rejection	$V_{IN} = \pm 10V_{DC}$	88	100		75	*		dB
	1N - ∓10 ADC	+	100			,	-	ub
OPEN-LOOP GAIN, DC	5		400					
Open-Loop Voltage Gain	$R_L \ge 1k\Omega$	88	100		75	*		dB
FREQUENCY RESPONSE								i
Gain Bandwidth	Gain = 100	4	6.5		3.5	*		MHz
Full-Power Response	20Vp-p, $R_L = 1kΩ$		570			*		kHz
Slew Rate	$V_O = \pm 10V, R_L = 1k\Omega$	24	35		20	*		V/µs
Settling Time:								
0.1%	Gain = -1 , $R_L = 1k\Omega$		0.6			*		μs
0.01%	$C_1 = 500 \text{pF}, 10 \text{V Step}$		1.0					μs
	OL = 300pi ; 10 v Step	_	1.0					μο
RATED OUTPUT	D 410	144.5	.400					.,
Voltage Output	$R_L = 1k\Omega$	±11.5	+12.9,		±11	*		V
_			-13.8					
Current Output	$V_O = \pm 10V_{DC}$	±15	±20		*	*		mA
Output Resistance	1MHz, Open Loop		80			*		Ω
oad Capacitance Stability	Gain = +1		1500			*		pF
Short-Circuit Current		±30	±50		±25	*		mA
POWER SUPPLY		1						
Rated Voltage			±15			*		V _{DC}
			1 13	140	,	*	,	
Voltage Range, Derated Performance	1 0 100	±5		±18	*	٠.	*	V _{DC}
Current, Quiescent	$I_O = 0mADC$		3	4		*	*	mA
Over Specified Temperature			3.5	4.5		*	*	mA
TEMPERATURE RANGE								ĺ
Specification	Ambient Temperature	-25		+85	*		*	°C
Operating:								1
P, U Packages		-25		+85	*		*	∘c
Storage:								
P, U Packages		-40		+125	*		*	∘c
9 _{JA}	I	200	1	0		1	°C/W	, –

 $[\]ensuremath{\texttt{*}}$ Same specifications as OPA602BP.

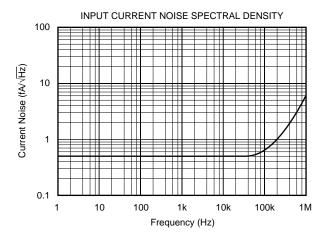
NOTE: (1) OPA602AP, AU ensured by design with a 99% confidence level.

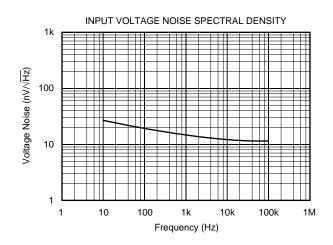


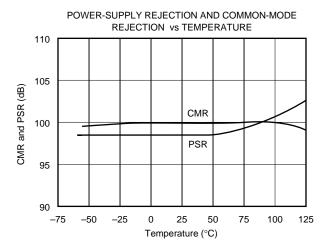


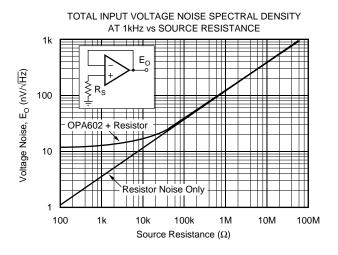
TYPICAL CHARACTERISTICS

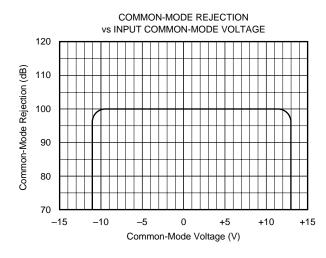
At $T_A = +25^{\circ}C$ and $V_S = \pm 15V_{DC}$, unless otherwise noted.

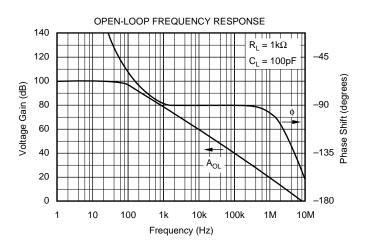








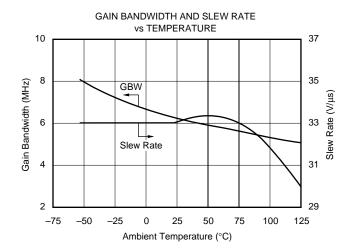


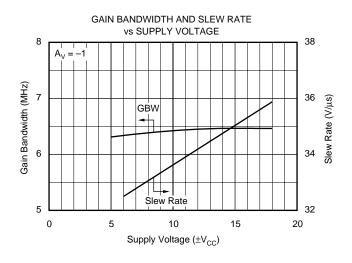


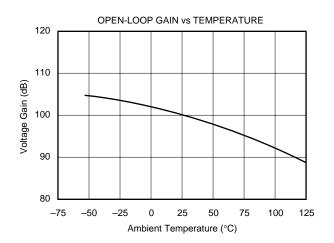


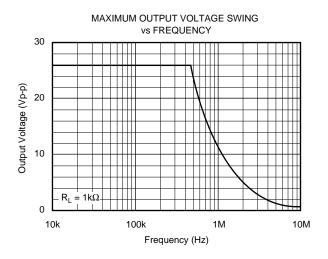
TYPICAL CHARACTERISTICS (Cont.)

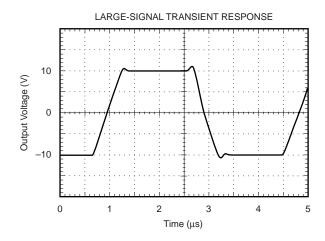
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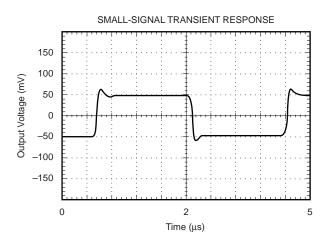










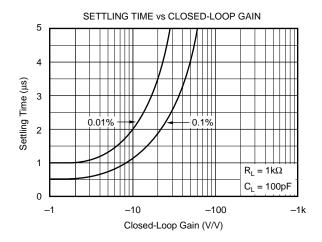


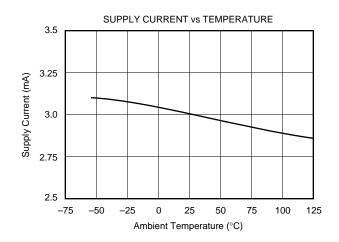


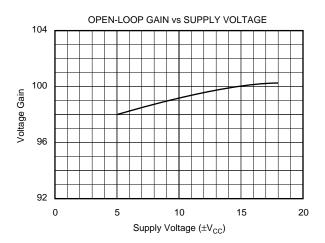


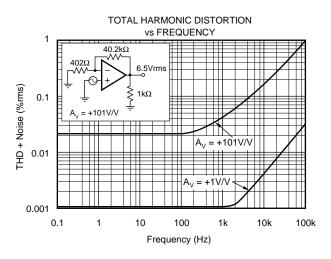
TYPICAL CHARACTERISTICS (Cont.)

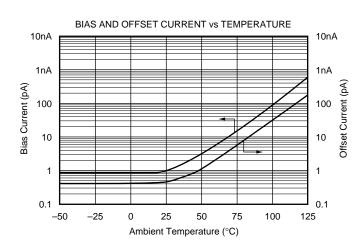
At $T_A = +25$ °C and $V_S = \pm 15 V_{DC}$, unless otherwise noted.

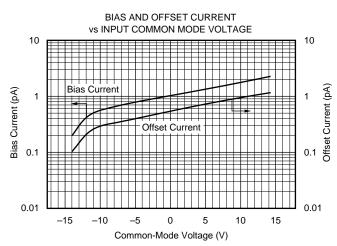








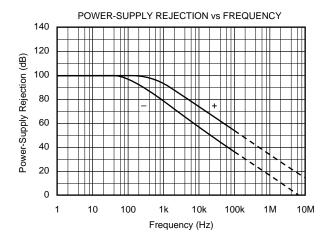


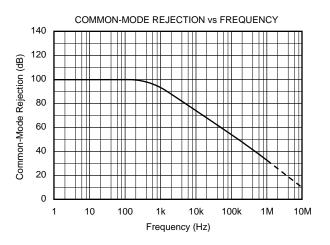




TYPICAL CHARACTERISTICS (Cont.)

At $T_A = +25$ °C and $V_S = \pm 15 V_{DC}$, unless otherwise noted.





APPLICATIONS INFORMATION

Unity-gain stability with good phase margin and excellent output drive characteristics bring freedom from the subtle problems associated with other high-speed amplifiers. However, as with any high-speed, wide bandwidth circuitry, careful circuit layout will ensure best performance. Make short, direct interconnections and avoid stray wiring capacitance—especially at the inverting input pin.

Power supplies should be bypassed with good high-frequency capacitors positioned close to the op amp pins. In most cases $0.1\mu F$ ceramic capacitors are adequate. Applications with heavier loads and fast transient waveforms may benefit from use of additional $1.0\mu F$ tantalum bypass capacitors.

INPUT BIAS CURRENT GUARDING

Leakage currents across printed circuit boards can easily exceed the input bias current of the OPA602. A circuit board "guard" pattern, as shown in Figure 1, is an effective solution to difficult leakage problems. This guard pattern must be repeated on all layers of a multilayer board. By surrounding critical high impedance input circuitry with a low impedance circuit connection at the same potential, leakage currents will flow harmlessly to the low-impedance node.

Input bias current may also be degraded by improper handling or cleaning. Contamination from handling parts and circuit boards may be cleaned with appropriate solvents and deionized water. Each rinsing operation should be followed by a 30-minute bake at +85°C.

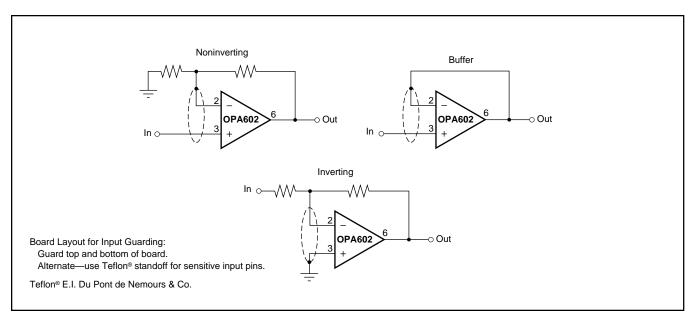


FIGURE 1. Connection of Input Guard.





APPLICATION CIRCUITS

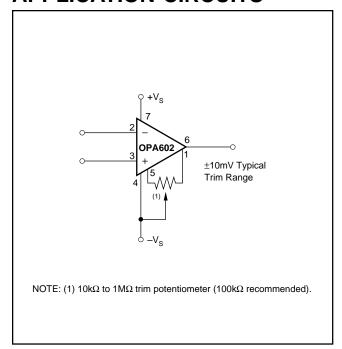


FIGURE 2. Offset Voltage Trim.

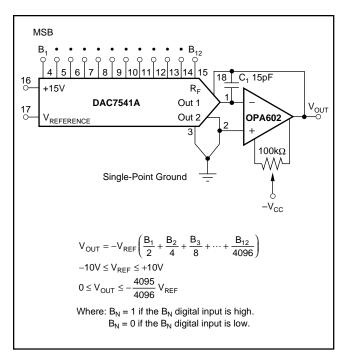


FIGURE 3. Voltage Output Digital-to-Analog Converter.

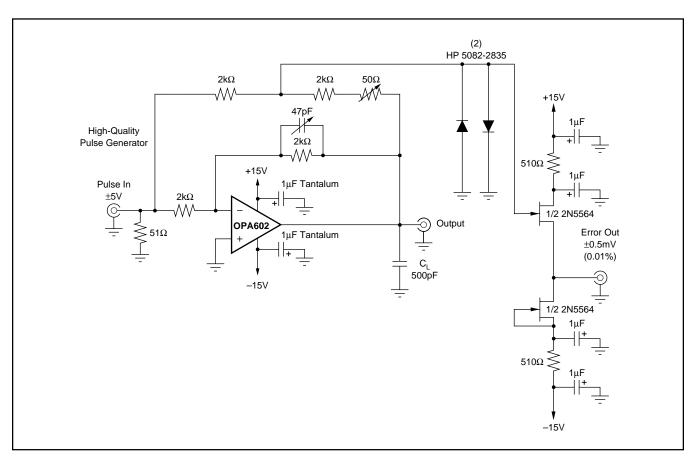
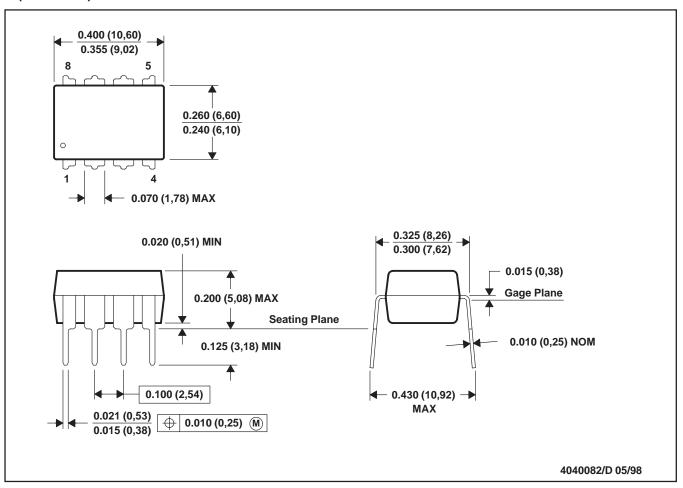


FIGURE 4. Settling Time and Slew Rate Test Circuit.

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE



NOTES: A. All linear dimensions are in inches (millimeters).

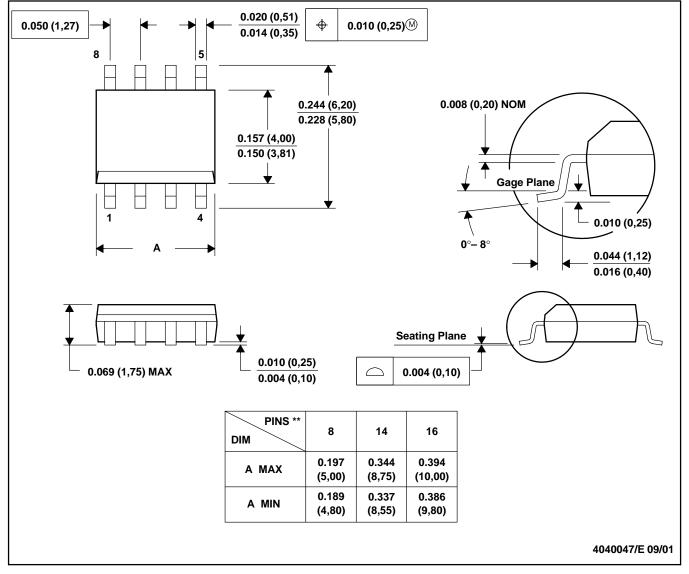
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001



D (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

8 PINS SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-012

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